

PATENT ABSTRACTS OF JAPAN

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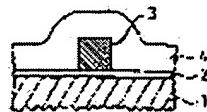
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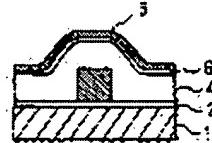
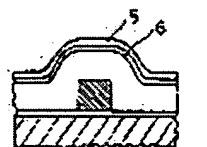
(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: To prevent uneven deformation of wiring on a protection film by providing a protection film consisting of a material having a higher melting point than that of interlayer insulation film between said interlayer insulation film and wiring arranged thereon.



CONSTITUTION: A semiconductor substrate 1, an insulation film 2, a lower wiring 3 and an interlayer insulating film 4 are sequentially formed. A protecting film 6 consisting of SiO₂ not including impurity such as phosphorus is deposited by the CVD method in the thickness of about 0.05μm on the interlayer insulation film consisting of phosphor glass under the reflow condition at about 1,000°C. An upper layer wiring 5 in the thickness of 0.1μm consisting of polysilicon is formed by reduced pressure CVD method on the protection film 6. Thereafter, the upper wiring 5 is annealed for 10min at 1,000°C under the nitrogen ambient. In this case, since SiO₂ of protection film 6 is not dissolved up to a temperature of 1,700°C, rigidity can be kept and the upper wiring 5 does not show uneven deformation.



LEGAL STATUS

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